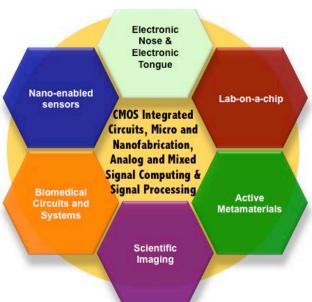
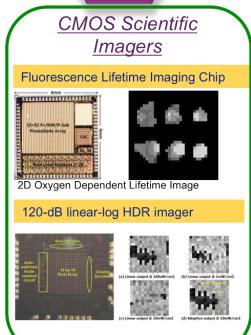
Sameer Sonkusale, Tufts University



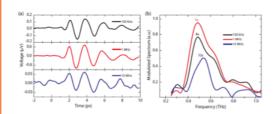


Active Metamaterial Modulators Modulation Gate Drain The Modulator Circuit model Transmitted Transmitted Active Metamaterial Transmitted Transmitted Active Metamaterial Transmitted Transmitted Transmitted

Hybridization of metamaterial with pHEMTs

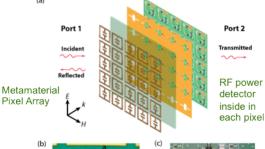
<u>Technology:</u> 0.5 um GaAs HEMT technology with 3200 periodic unit cells on area of 2.7×2.6 mm²

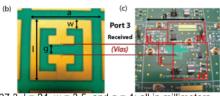
<u>Results:</u> THz time-domain spectrometer (THz-TDS) characterization shows resonance frequency of 0.46 THz and modulation index of over 30% for frequency >10 MHz



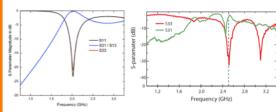
(a) Transmitted time dependent electric field for modulation at frequencies of 100 kHz, 1 MHz and 10 MHz. (b) Transmitted spectra calculated from the time domain data.

Active Metamaterial Detectors/Imagers

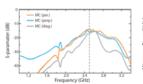




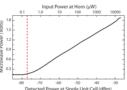
a = 27.3, l = 24, w = 3.5, and g = 4; all in millimeters.



Reflection coefficient (S_{33} red curve) and the transmission (S_{31} green curve) with the dashed grey line at 2.5 GHz, which is the resonant frequency.



Mutual coupling between neighboring unit cells metrics of pixel channel independence



Sensitivity as function of incident radiation power Result > -77dBm @2.5 GHz